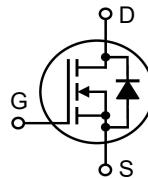


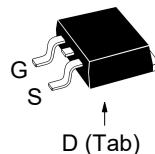
**X4-Class  
Power MOSFET™**
**IXTA94N20X4**

**V<sub>DSS</sub>** = 200V  
**I<sub>D25</sub>** = 94A  
**R<sub>DS(on)</sub>** ≤ 10.6mΩ

N-Channel Enhancement Mode  
Avalanche Rated



**TO-263  
(IXTA)**



G = Gate      D = Drain  
 S = Source      Tab = Drain

<b>Symbol</b>	<b>Test Conditions</b>	<b>Maximum Ratings</b>	
<b>V<sub>DSS</sub></b>	T <sub>J</sub> = 25°C to 175°C	200	V
<b>V<sub>DGR</sub></b>	T <sub>J</sub> = 25°C to 175°C, R <sub>GS</sub> = 1MΩ	200	V
<b>V<sub>GSS</sub></b>	Continuous	±20	V
<b>V<sub>GSM</sub></b>	Transient	±30	V
<b>I<sub>D25</sub></b>	T <sub>C</sub> = 25°C	94	A
<b>I<sub>DM</sub></b>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	220	A
<b>I<sub>A</sub></b>	T <sub>C</sub> = 25°C	47	A
<b>E<sub>AS</sub></b>	T <sub>C</sub> = 25°C	1	J
<b>dv/dt</b>	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	20	V/ns
<b>P<sub>D</sub></b>	T <sub>C</sub> = 25°C	360	W
<b>T<sub>J</sub></b>		-55 ... +175	°C
<b>T<sub>JM</sub></b>		175	°C
<b>T<sub>stg</sub></b>		-55 ... +15	°C
<b>T<sub>SOLD</sub></b>	Plastic Body for 10s	260	°C
<b>F<sub>c</sub></b>	Mounting Force	10..65 / 2.2..14.6	N/lb
<b>Weight</b>		2.5	g

**Symbol      Test Conditions**  
(T<sub>J</sub> = 25°C, Unless Otherwise Specified)

<b>Symbol</b>	<b>Test Conditions</b>	<b>Characteristic Values</b>		
		<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>
<b>BV<sub>DSS</sub></b>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	200		V
<b>V<sub>GS(th)</sub></b>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.5		4.5 V
<b>I<sub>GSS</sub></b>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100 nA
<b>I<sub>DSS</sub></b>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 150°C			20 μA 500 μA
<b>R<sub>DS(on)</sub></b>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Notes 1 & 2			10.6 mΩ

Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1	60	100	S
<b>R<sub>Gi</sub></b>	Gate Input Resistance		5.3	Ω
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz	5050		pF
<b>C<sub>oss</sub></b>		750		pF
<b>C<sub>rss</sub></b>		4		pF
<b>Effective Output Capacitance</b>				
<b>C<sub>o(er)</sub></b>	Energy related } V <sub>GS</sub> = 0V	390		pF
<b>C<sub>o(tr)</sub></b>	Time related } V <sub>DS</sub> = 0.8 • V <sub>DSS</sub>	1670		pF
<b>t<sub>d(on)</sub></b>	Resistive Switching Times V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 5Ω (External)	18		ns
<b>t<sub>r</sub></b>		9		ns
<b>t<sub>d(off)</sub></b>		97		ns
<b>t<sub>f</sub></b>		7		ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>	77		nC
<b>Q<sub>gs</sub></b>		21		nC
<b>Q<sub>gd</sub></b>		25		nC
<b>R<sub>thJC</sub></b>			0.42	°C/W

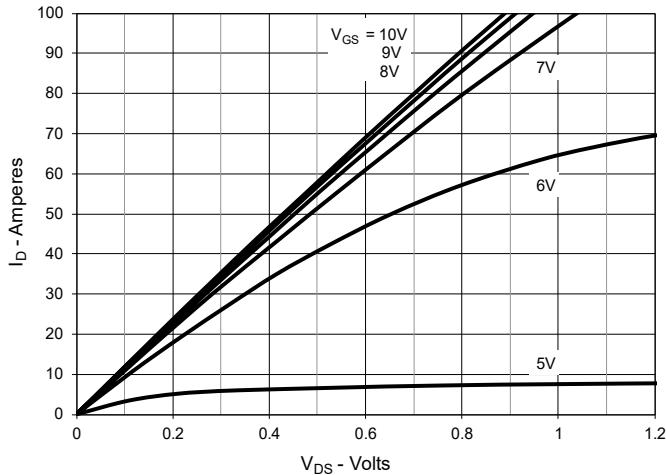
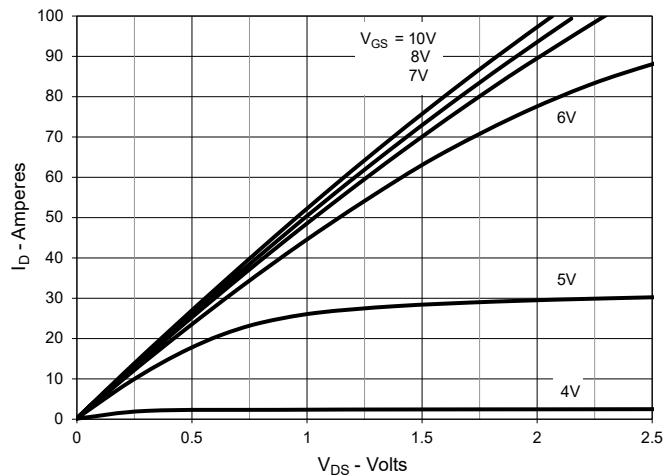
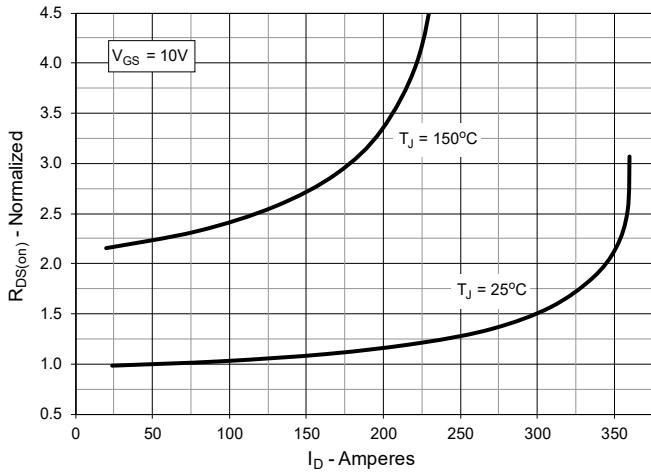
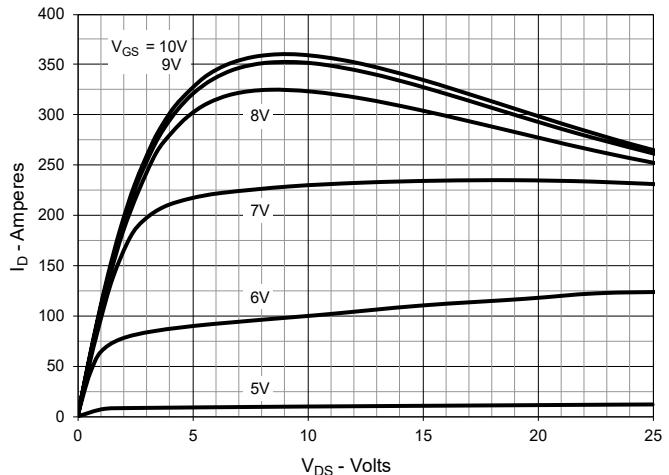
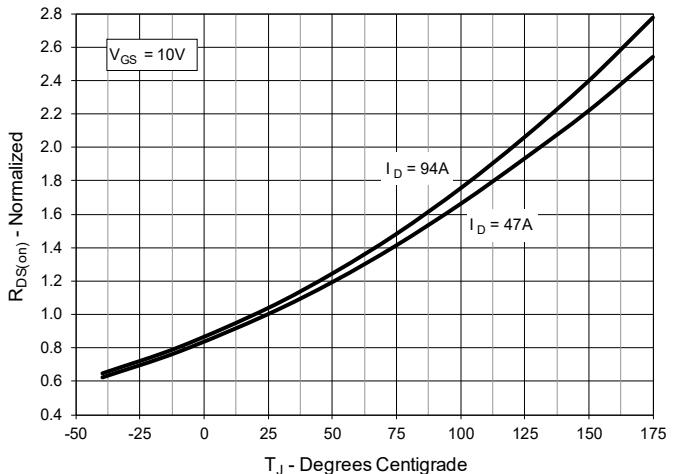
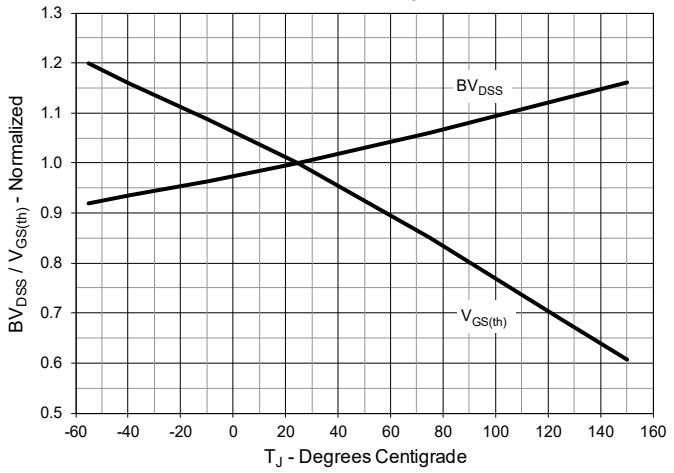
### Source-Drain Diode

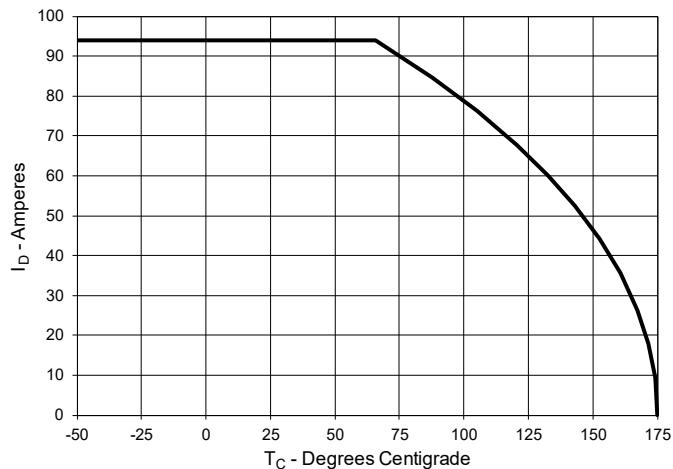
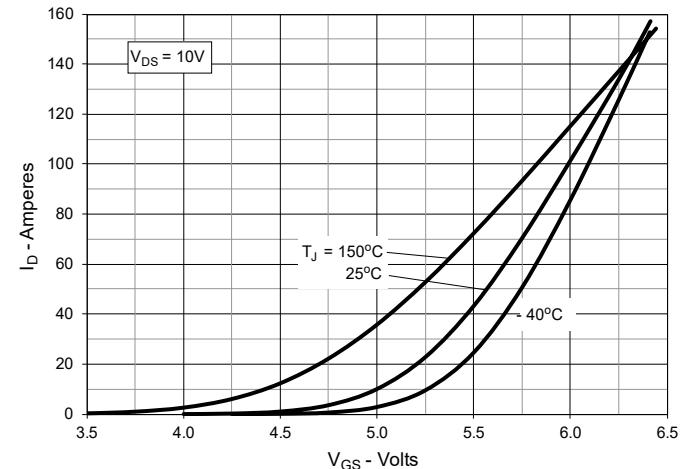
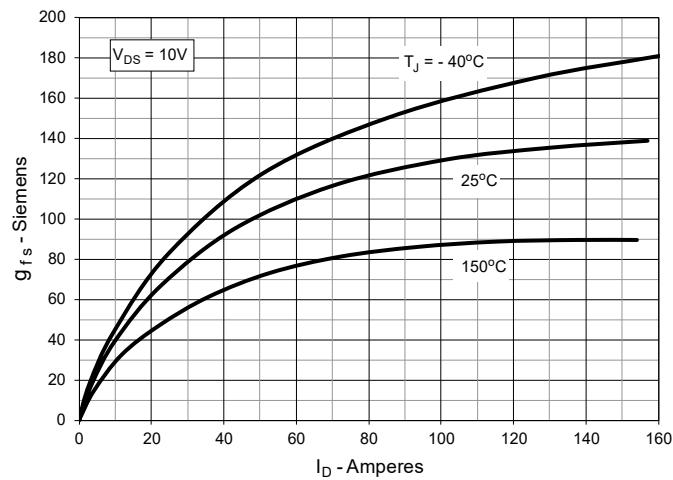
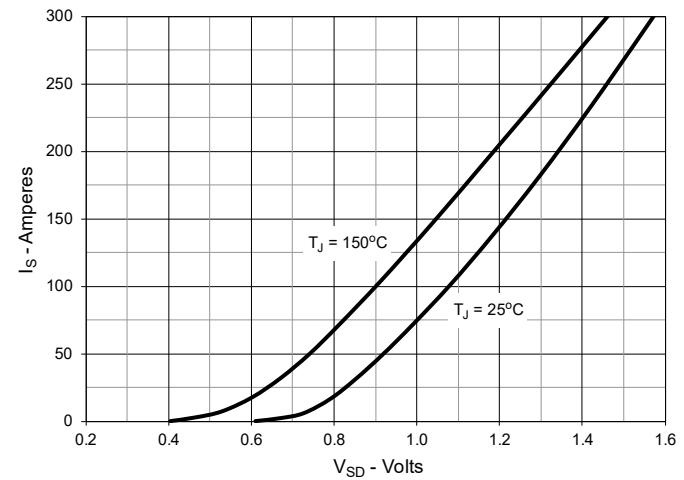
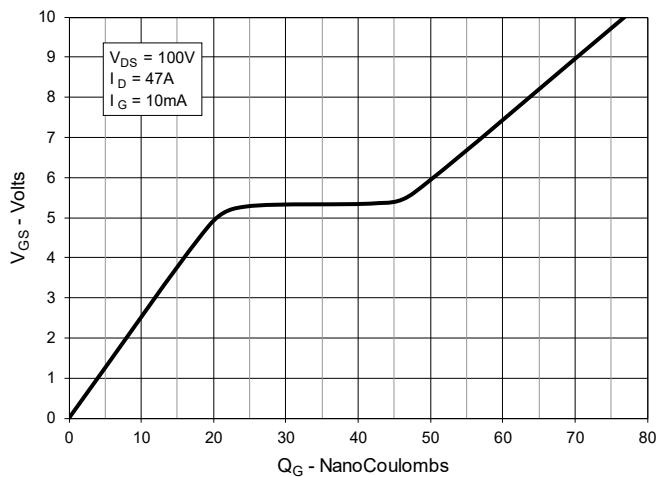
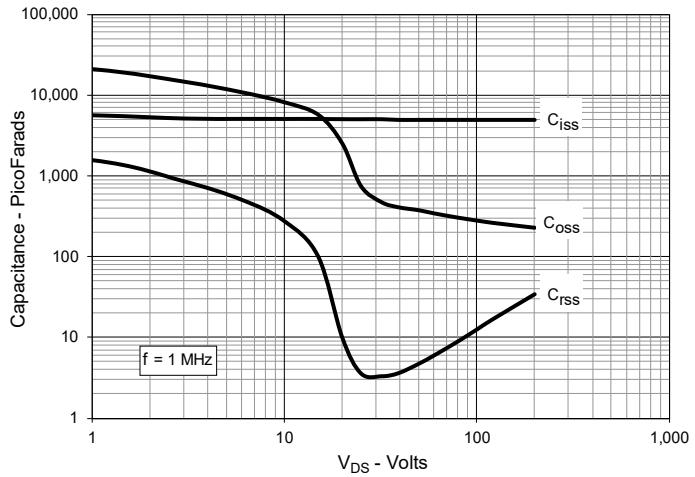
Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
<b>I<sub>s</sub></b>	V <sub>GS</sub> = 0V		94	A
<b>I<sub>SM</sub></b>	Repetitive, pulse Width Limited by T <sub>JM</sub>		376	A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>s</sub> , V <sub>GS</sub> = 0V, Note 1		1.4	V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 47A, -di/dt = 200A/μs V <sub>R</sub> = 100V	130		ns
<b>Q<sub>RM</sub></b>		1.1		μC
<b>I<sub>RM</sub></b>		17		A

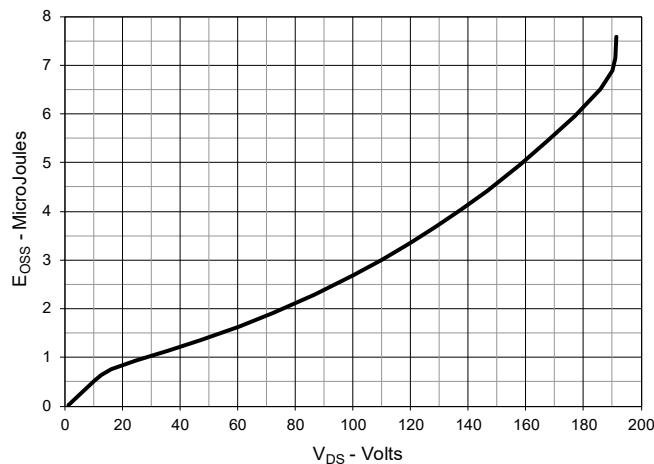
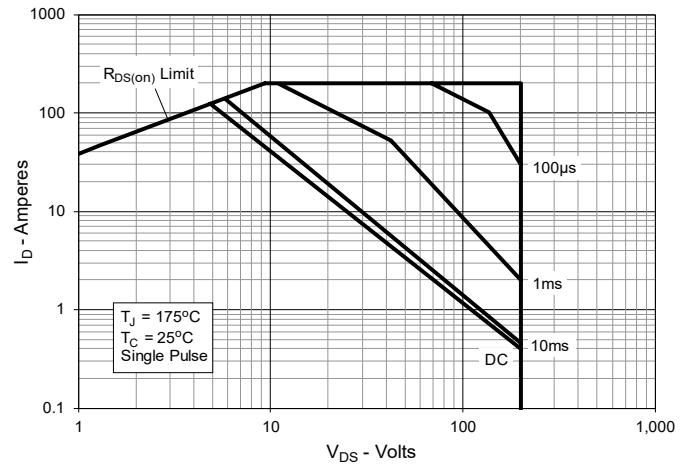
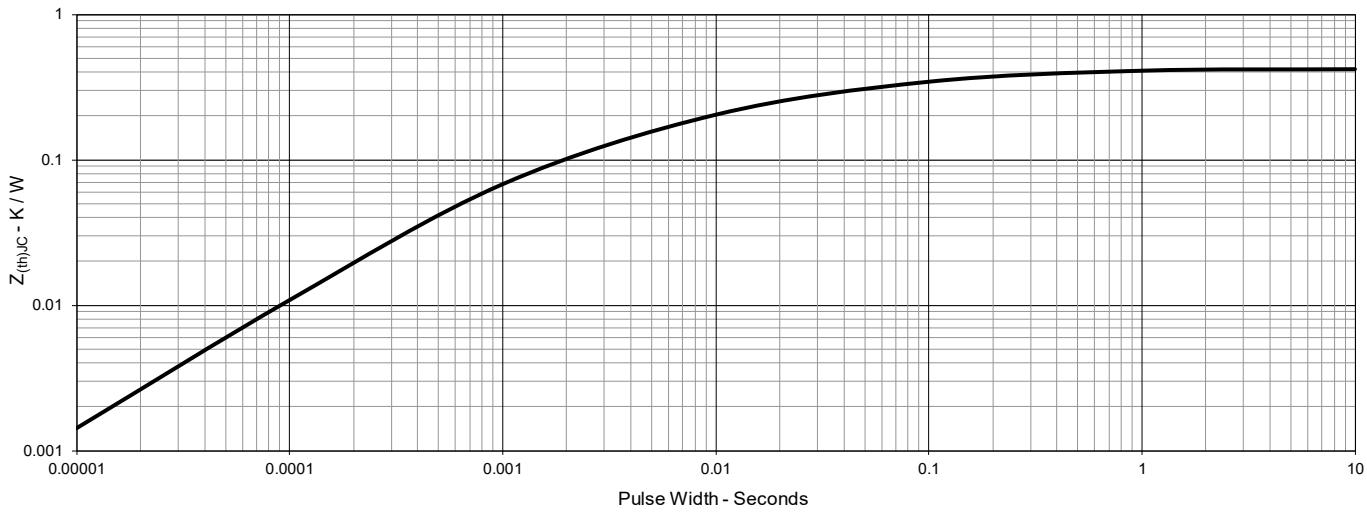
- Notes:
1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
  2. On through-hole packages, R<sub>DS(on)</sub> Kelvin test contact location must be 5mm or less from the package body.

Littelfuse reserves the right to change limits, test conditions and dimensions.

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**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** **Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$** **Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 47\text{A}$  Value vs. Drain Current****Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** **Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 47\text{A}$  Value vs. Junction Temperature****Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**

**Fig. 7. Maximum Drain Current vs. Case Temperature****Fig. 8. Input Admittance****Fig. 9. Transconductance****Fig. 10. Forward Voltage Drop of Intrinsic Diode****Fig. 11. Gate Charge****Fig. 12. Capacitance**

**Fig. 13. Output Capacitance Stored Energy****Fig. 14. Forward-Bias Safe Operating Area****Fig. 15. Maximum Transient Thermal Impedance**

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
E2	.100	BSC	2.54	BSC
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010	BSC	0.254	BSC

**TO-263 Outline**

**1 - Gate**  
**2,4 - Drain**  
**3 - Source**

**NOTE:**

1. This drawing meets all dimensions requirement of JEDEC outlines TO-263AB.
2. All metal surface are matte pure tin plated except trimmed area.
3. **L** is Gauge plane to measure **L**.
4. These dimension do not include mold flash and they will not exceed 0.005[0.13] per side.

MINIMUM PCB FOOT PRINT LAYOUT



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